

# Etienne Gheeraert

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

145  
papers

3,402  
citations

31  
h-index

49  
g-index

150  
ext. papers

3,644  
ext. citations

3.1  
avg, IF

4.66  
L-index

#	Paper	IF	Citations
145	. <i>IEEE Transactions on Electron Devices</i> , <b>2021</b> , 1-7	2.9	2
144	Diamond/Alumina band offset determination by XPS. <i>Applied Surface Science</i> , <b>2021</b> , 535, 146301	6.7	3
143	Study of ion-implanted nitrogen related defects in diamond Schottky barrier diode by transient photocapacitance and photoluminescence spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SBBD07	1.4	1
142	Comparative study of two atomic layer etching processes for GaN. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2020</b> , 38, 032602	2.9	8
141	Analysis of InGaN surfaces after chemical treatments and atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> for QLED applications <b>2020</b> ,		2
140	High quality Al <sub>2</sub> O <sub>3</sub> /(100) oxygen-terminated diamond interface for MOSFETs fabrication. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 102103	3.4	15
139	Impact of Nonhomoepitaxial Defects in Depleted Diamond MOS Capacitors. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 1830-1837	2.9	5
138	Electric field distribution using floating metal guard rings edge-termination for Schottky diodes. <i>Diamond and Related Materials</i> , <b>2018</b> , 82, 160-164	3.5	11
137	Comprehensive electrical analysis of metal/Al <sub>2</sub> O <sub>3</sub> /O-terminated diamond capacitance. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 161523	2.5	23
136	Gate Oxide Electrical Stability of p-type Diamond MOS Capacitors. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 3361-3364	2.9	8
135	Electric Field Characterization of Diamond Metal Semiconductor Field Effect Transistors Using Electron Beam Induced Current. <i>Materials Science Forum</i> , <b>2018</b> , 924, 935-938	0.4	
134	Carbon nanotube forest based electrostatic capacitor with excellent dielectric performances. <i>Carbon</i> , <b>2017</b> , 116, 648-654	10.4	26
133	Characterization of breakdown behavior of diamond Schottky barrier diodes using impact ionization coefficients. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CR12	1.4	7
132	Defect and field-enhancement characterization through electron-beam-induced current analysis. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 182103	3.4	12
131	Deep depletion concept for diamond MOSFET. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 173503	3.4	33
130	Deep-Depletion Mode Boron-Doped Monocrystalline Diamond Metal Oxide Semiconductor Field Effect Transistor. <i>IEEE Electron Device Letters</i> , <b>2017</b> , 38, 1571-1574	4.4	39
129	<b>2017</b> ,		5

128	Mechanism of reverse current increase of vertical-type diamond Schottky diodes. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 135304	2.5	15
127	Recent progress on diamond Schottky diode <b>2016</b> ,		4
126	Effects of high-power laser irradiation on sub-superficial graphitic layers in single-crystal diamond. <i>Acta Materialia</i> , <b>2016</b> , 103, 665-671	8.4	10
125	Energy-band diagram configuration of Al <sub>2</sub> O <sub>3</sub> /oxygen-terminated p-diamond metal-oxide-semiconductor. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 141601	3.4	32
124	Hole injection contribution to transport mechanisms in metal/p <sup>+</sup> p <sup>++</sup> and metal/oxide/p <sup>+</sup> p <sup>++</sup> diamond structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 2501-2506	1.6	3
123	Zr/oxidized diamond interface for high power Schottky diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 052105	5.4	91
122	Doping and interface of homoepitaxial diamond for electronic applications. <i>MRS Bulletin</i> , <b>2014</b> , 39, 499-503	5.2	43
121	Diamond as substrate for 3C-SiC growth: A TEM study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 2302-2306	1.6	
120	Model implementation towards the prediction of J(V) characteristics in diamond bipolar device simulations. <i>Diamond and Related Materials</i> , <b>2014</b> , 43, 34-42	3.5	19
119	A composite material made of carbon nanotubes partially embedded in a nanocrystalline diamond film. <i>Carbon</i> , <b>2013</b> , 52, 408-417	10.4	16
118	Etching mechanism of diamond by Ni nanoparticles for fabrication of nanopores. <i>Carbon</i> , <b>2013</b> , 59, 448-456	4.6	40
117	Metal oxide semiconductor structure using oxygen-terminated diamond. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 242108	3.4	44
116	Synchronized B and <sup>13</sup> C Diamond Delta Structures for an Ultimate In-Depth Chemical Characterization. <i>Applied Physics Express</i> , <b>2013</b> , 6, 045801	2.4	17
115	In situ etching-back processes for a sharper top interface in boron delta-doped diamond structures. <i>Diamond and Related Materials</i> , <b>2012</b> , 24, 175-178	3.5	19
114	Formation of oriented nanostructures in diamond using metallic nanoparticles. <i>Nanotechnology</i> , <b>2012</b> , 23, 455302	3.4	27
113	Hole transport in boron delta-doped diamond structures. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 162101	3.4	28
112	Diamond nanophotonics. <i>Beilstein Journal of Nanotechnology</i> , <b>2012</b> , 3, 895-908	3	23
111	Investigation of nickel lattice sites in diamond: Density functional theory and x-ray absorption near-edge structure experiments. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	4

110	High-field magnetospectroscopy to probe the 1.4-eV Ni color center in diamond. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	2
109	Bottom-up fabrication of diamond nanowire arrays. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 779-781	3.5	12
108	Dry etching of diamond nanowires using self-organized metal droplet masks. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 389-394	3.5	23
107	Behavior of CVD diamond-based TL dosimeters in radiotherapy environments using photon and electron beams from treatment accelerators. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 520-522	3.5	1
106	Ultra-smooth single crystal diamond surfaces resulting from implantation and lift-off processes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2011</b> , 208, 2057-2061	1.6	7
105	Simulations of carrier confinement in boron doped diamond devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 2084-2087	1.6	20
104	Doping of single crystalline diamond with nickel. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 2054-2057	1.6	9
103	Magneto-optical spectroscopy of (Ga,Mn)N epilayers. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	26
102	Hall electron mobility in diamond. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 122111	3.4	60
101	Intrinsic magnetism in wurtzite (Ga,Mn)N. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 4062-4065		3
100	Magneto-optical spectroscopy of the wide band gap diluted magnetic semiconductor GaMnN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2006</b> , 126, 240-244	3.1	3
99	{111}-oriented diamond films and p/n junctions grown on B-doped type Ib substrates. <i>Diamond and Related Materials</i> , <b>2005</b> , 14, 522-525	3.5	10
98	High-resolution spectroscopic investigation of the Mn centre in GaN. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e2233-e2237	1.6	2
97	Spin Carrier Exchange Interactions in (Ga,Mn)N and (Zn,Co)O Wide Band Gap Diluted Magnetic Semiconductor Epilayers. <i>Journal of Superconductivity and Novel Magnetism</i> , <b>2005</b> , 18, 15-21		15
96	Superconductivity in boron-doped homoepitaxial (001)-oriented diamond layers. <i>Physica Status Solidi A</i> , <b>2005</b> , 202, 2160-2165		18
95	Micro-Raman scattering from undoped and phosphorous-doped (111) homoepitaxial diamond films: Stress imaging of cracks. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 043530	2.5	29
94	Study of the phosphorus incorporation in n-doped diamond films by cathodoluminescence. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S287-S292	1.8	7
93	Internal stresses in {111} homoepitaxial CVD diamond. <i>Diamond and Related Materials</i> , <b>2004</b> , 13, 329-334	3.5	9

92	Characterization of <111> diamond thin films by micro-Raman spectroscopy. <i>Diamond and Related Materials</i> , <b>2004</b> , 13, 886-890	3.5	8
91	Homoepitaxial {111}-oriented diamond pn junctions grown on B-doped Ib synthetic diamond. <i>Physica Status Solidi A</i> , <b>2004</b> , 201, 2462-2466		27
90	Dependence of the superconducting transition temperature on the doping level in single-crystalline diamond films. <i>Physical Review Letters</i> , <b>2004</b> , 93, 237005	7.4	172
89	Strains and cracks in undoped and phosphorus-doped {111} homoepitaxial diamond films. <i>Physica Status Solidi A</i> , <b>2003</b> , 199, 87-91		17
88	Optical and electronic properties of heavily boron-doped homo-epitaxial diamond. <i>Physica Status Solidi A</i> , <b>2003</b> , 199, 9-18		96
87	DC current and AC impedance measurements on boron-doped single crystalline diamond films. <i>Physica Status Solidi A</i> , <b>2003</b> , 199, 92-96		10
86	Study of aluminium nitride/freestanding diamond surface acoustic waves filters. <i>Diamond and Related Materials</i> , <b>2003</b> , 12, 723-727	3.5	24
85	Charge-based deep level transient spectroscopy of phosphorous-doped homoepitaxial diamond. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 5832-5843	2.5	8
84	Characterization of n-Type Doped Homoepitaxial Diamond Thin Films. <i>Physica Status Solidi A</i> , <b>2002</b> , 193, 541-545		23
83	Radiation tolerance of CVD diamond detectors for pions and protons. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2002</b> , 476, 686-693	1.2	25
82	Performance of irradiated CVD diamond micro-strip sensors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2002</b> , 476, 706-712	1.2	11
81	Electrical and optical measurements of CVD diamond doped with sulfur. <i>Physical Review B</i> , <b>2002</b> , 65,	3.3	19
80	Thermoluminescent properties of Ni and Co doped synthetic, high pressure, high temperature diamonds: application to ionising radiation dosimetry. <i>Radiation Protection Dosimetry</i> , <b>2002</b> , 100, 329-32 <sup>0.9</sup>		9
79	A new acceptor state in CVD-diamond. <i>Diamond and Related Materials</i> , <b>2002</b> , 11, 347-350	3.5	14
78	Epitaxial growth of phosphorus doped diamond on {111} substrate. <i>Diamond and Related Materials</i> , <b>2002</b> , 11, 328-331	3.5	15
77	n-Type doping of diamond by sulfur and phosphorus. <i>Diamond and Related Materials</i> , <b>2002</b> , 11, 289-295	3.5	53
76	Etching of p- and n-type doped monocrystalline diamond using an ECR oxygen plasma source. <i>Diamond and Related Materials</i> , <b>2002</b> , 11, 828-832	3.5	13
75	Diamond Pixel Detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2001</b> , 465, 88-91	1.2	9

74	Effect of Magnetic Field on Phosphorus Centre in Diamond. <i>Physica Status Solidi A</i> , <b>2001</b> , 186, 291-295		6
73	Low temperature excitation spectrum of phosphorus in diamond. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 444-448	3.5	35
72	Conductivity and photoconductivity in boron doped diamond films: Microwave measurements. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 4251-4255	2.5	1
71	Phosphorus site after CIRA implantation of type IIa diamond. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 580-584	3.5	5
70	CVD diamond sensors for charged particle detection. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 1778-1782	3.5	12
69	Hydrogen diffusion in B-ion-implanted and B-doped homo-epitaxial diamond: passivation of defects vs. passivation of B acceptors. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 453-458	3.5	39
68	Phonon-assisted electronic transitions in phosphorus-doped n-type chemical vapor deposition diamond films. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 439-443	3.5	26
67	Hydrogen-acceptor interactions in diamond. <i>Diamond and Related Materials</i> , <b>2001</b> , 10, 399-404	3.5	48
66	ESR Study of Phosphorus Implanted Type IIa Diamond. <i>Physica Status Solidi A</i> , <b>2000</b> , 181, 5-10		12
65	Electronic transitions of electrons bound to phosphorus donors in diamond. <i>Solid State Communications</i> , <b>2000</b> , 113, 577-580	1.6	69
64	Pulse height distribution and radiation tolerance of CVD diamond detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2000</b> , 447, 244-250	1.2	31
63	Micro-strip sensors based on CVD diamond. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>2000</b> , 453, 141-148	1.2	16
62	Thermoluminescence of nickel-doped synthetic diamond crystals. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 4648	2.5	12
61	Characterisation by thermoluminescence of boron doped polycrystalline diamond films. <i>Diamond and Related Materials</i> , <b>2000</b> , 9, 56-60	3.5	13
60	Electronic states of phosphorus in diamond. <i>Diamond and Related Materials</i> , <b>2000</b> , 9, 948-951	3.5	60
59	Temperature dependent spectroscopic study of the electronic structure of phosphorus in n-type CVD diamond films. <i>Diamond and Related Materials</i> , <b>2000</b> , 9, 952-955	3.5	18
58	Recent results with CVD diamond trackers. <i>Nuclear Physics, Section B, Proceedings Supplements</i> , <b>1999</b> , 78, 329-334		2
57	CVD diamond pixel detectors for LHC experiments. <i>Nuclear Physics, Section B, Proceedings Supplements</i> , <b>1999</b> , 78, 497-504		3

56	Parameterisation of radiation effects on CVD diamond for proton irradiation. <i>Nuclear Physics, Section B, Proceedings Supplements, 1999, 78, 675-682</i>		5
55	Review of the development of diamond radiation sensors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 434, 131-145</i>	1.2	52
54	The first bump-bonded pixel detectors on CVD diamond. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 436, 326-335</i>	1.2	18
53	CVD diamond detectors for ionizing radiation. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 435, 194-201</i>	1.2	22
52	Proton irradiation of CVD diamond detectors for high-luminosity experiments at the LHC. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 426, 173-180</i>	1.2	55
51	Influence of diborane on the growth rate and phase stability of diamond films. <i>Carbon, 1999, 37, 107-111</i>	10.4	18
50	A large range of boron doping with low compensation ratio for homoepitaxial diamond films. <i>Carbon, 1999, 37, 807-810</i>	10.4	60
49	Thermally Stimulated Conductivity and Luminescence in Polycrystalline Diamond Films. <i>Physica Status Solidi A, 1999, 172, 183-192</i>		22
48	Deep Level Spectroscopy in Homoepitaxial Diamond Films Studied from Current Transients in Schottky Junctions. <i>Physica Status Solidi A, 1999, 174, 129-135</i>		9
47	Electronic States of Boron and Phosphorus in Diamond. <i>Physica Status Solidi A, 1999, 174, 39-51</i>		68
46	Low Temperature Photoconductivity Detection of Phosphorus in Diamond. <i>Physica Status Solidi A, 1999, 174, 53-58</i>		16
45	Hydrogen in Monocrystalline CVD Boron Doped Diamond. <i>Physica Status Solidi A, 1999, 174, 73-81</i>		37
44	Study of the Electronic Structure of the Phosphorus Level in n-Type CVD Diamond. <i>Physica Status Solidi A, 1999, 174, R1-R2</i>		6
43	Photocapacitance study of boron-doped chemical-vapor-deposited diamond. <i>Physical Review B, 1999, 60, 2476-2479</i>	3.3	17
42	Carbide contacts on homoepitaxial diamond films. <i>Diamond and Related Materials, 1999, 8, 961-965</i>	3.5	19
41	Tracking with CVD diamond radiation sensors at high luminosity colliders. <i>IEEE Transactions on Nuclear Science, 1999, 46, 193-200</i>	1.7	13
40	Evidence of hydrogen-boron interactions in diamond from deuterium diffusion and infrared spectroscopy experiments. <i>Diamond and Related Materials, 1999, 8, 278-282</i>	3.5	8
39	Thermally Stimulated Conductivity and Luminescence in Polycrystalline Diamond Films <b>1999, 172, 183</b>		1

38	Electronic States of Boron and Phosphorus in Diamond <b>1999</b> , 174, 39		3
37	Status of diamond particle detectors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1998</b> , 418, 196-202	1.2	10
36	Recent results on CVD diamond radiation sensors. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , <b>1998</b> , 409, 264-270 <sup>1,2</sup>		24
35	The effect of boron doping on the lattice parameter of homoepitaxial diamond films. <i>Diamond and Related Materials</i> , <b>1998</b> , 7, 869-873	3.5	38
34	Activation energy in low compensated homoepitaxial boron-doped diamond films. <i>Diamond and Related Materials</i> , <b>1998</b> , 7, 1390-1393	3.5	161
33	Hydrogen-boron interactions in p-type diamond. <i>Physical Review B</i> , <b>1998</b> , 58, 7966-7969	3.3	115
32	Boron-related infra-red absorption in homoepitaxial diamond films. <i>Diamond and Related Materials</i> , <b>1998</b> , 7, 1509-1512	3.5	56
31	Microstructure evolution of boron doped homoepitaxial diamond films. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 181-186	2.5	19
30	Hydrogen Diffusion in Boron Doped Diamond: Evidence of Hydrogen-Boron Interactions. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 510, 169		6
29	Variation of the cell parameter of polycrystalline boron doped diamond films. <i>Journal of Applied Physics</i> , <b>1997</b> , 81, 1120-1125	2.5	31
28	Effect of boron incorporation on the structure of polycrystalline diamond films. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 774-777	3.5	17
27	A two-step process for the formation of a Mo <sub>2</sub> C contact on polycrystalline diamond films. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 843-846	3.5	3
26	Nitrogen doping of diamond by ion implantation. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 516-520	3.5	44
25	Minimization of the defects concentration from boron incorporation in polycrystalline diamond films. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 778-782	3.5	19
24	Formation and resistivity of Mo <sub>2</sub> C on polycrystalline diamond according to the preparation conditions. <i>Diamond and Related Materials</i> , <b>1996</b> , 5, 779-783	3.5	6
23	Conduction mechanisms in boron implanted diamond films. <i>Diamond and Related Materials</i> , <b>1996</b> , 5, 752-756		18
22	Concentration of paramagnetic centers in boron doped polycrystalline diamond films. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 2123-2125	3.4	8
21	Effect of boron incorporation on the lattice parameter and texture of diamond films deposited by chemical vapour deposition on silicon. <i>Journal of Crystal Growth</i> , <b>1995</b> , 148, 110-115	1.6	13



20	Raman study of diamond films deposited by MPCVD: effect of the substrate position. <i>Thin Solid Films</i> , <b>1995</b> , 256, 13-22	2.2	10
19	Electrical conduction and deep levels in polycrystalline diamond films. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 6633-6638	2.5	61
18	Chemical vapor deposition of B-doped polycrystalline diamond films: Growth rate and incorporation efficiency of dopants. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 7404-7406	2.5	20
17	Photoconductivity associated with deep levels in polycrystalline diamond films. <i>Philosophical Magazine Letters</i> , <b>1995</b> , 72, 257-261	1	3
16	Characterization of heavily B-doped polycrystalline diamond films using Raman spectroscopy and electron spin resonance. <i>Journal of Applied Physics</i> , <b>1995</b> , 78, 7059-7062	2.5	124
15	Determination of weak optical absorption coefficients in polycrystalline diamond thin films by photothermal deflection spectroscopy. <i>Diamond and Related Materials</i> , <b>1995</b> , 4, 684-687	3.5	5
14	Annealing of diamond above 800 °C: need for and results of Si <sub>3</sub> N <sub>4</sub> encapsulation. <i>Diamond and Related Materials</i> , <b>1995</b> , 4, 596-599	3.5	1
13	Metal/insulator/semiconductor tunnel diodes formed by the oxidation of polycrystalline diamond films. <i>Journal of Applied Physics</i> , <b>1994</b> , 76, 3929-3931	2.5	8
12	Influence of annealing on the resistance of polycrystalline chemically vapour deposited diamond films: a surface chemical effect. <i>Diamond and Related Materials</i> , <b>1994</b> , 3, 654-657	3.5	7
11	Reality of doping by boron implantation of CVD polycrystalline diamond from a comparison of Raman and electrical measurements. <i>Diamond and Related Materials</i> , <b>1994</b> , 3, 623-627	3.5	20
10	Characterization of defects in boron implanted chemically vapour deposited diamond films by electron paramagnetic resonance and cathodoluminescence. <i>Diamond and Related Materials</i> , <b>1994</b> , 3, 737-740	3.5	14
9	Spectral response of the photoconductivity of polycrystalline chemically vapor deposited diamond films. <i>Diamond and Related Materials</i> , <b>1994</b> , 3, 836-839	3.5	10
8	. <i>IEEE Transactions on Nuclear Science</i> , <b>1994</b> , 41, 927-932	1.7	32
7	Characterization of CVD Diamond Films Used for Radiation Detection.. <i>Materials Research Society Symposia Proceedings</i> , <b>1994</b> , 339, 185		1
6	Effect of boron incorporation on the quality of MPCVD diamond films. <i>Diamond and Related Materials</i> , <b>1993</b> , 2, 742-745	3.5	80
5	The influence of oxygen, in gas mixtures and various substrate positions, on the broad cathodoluminescence bands of MPCVD diamond films. <i>Diamond and Related Materials</i> , <b>1993</b> , 2, 737-741	3.5	20
4	Tungsten incorporation in diamond thin films prepared by the hotfilament technique. <i>Diamond and Related Materials</i> , <b>1992</b> , 1, 504-507	3.5	18
3	Defects and stress analysis of the Raman spectrum of diamond films. <i>Diamond and Related Materials</i> , <b>1992</b> , 1, 525-528	3.5	51

- 2 IR characterization of diamond films on Si substrates. *Diamond and Related Materials*, **1992**, 1, 584-587 3.5 27
- 1 Electronic characterization of new c-Si/a-Si:H/Pt thin film devices. *Thin Solid Films*, **1989**, 174, 203-207 2.2